



**DMG3402L** 

#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
	$52m\Omega @ V_{GS} = 10V$	4A
30V	$65m\Omega$ @ $V_{GS} = 4.5V$	3A
	$85m\Omega @ V_{GS} = 2.5V$	2A

#### **Features**

- Low On-Resistance:
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Applications**

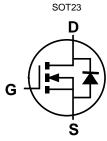
- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays

#### **Mechanical Data**

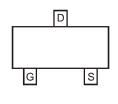
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)







**Equivalent Circuit** 



Pin Configuration

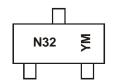
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMG3402L-7	SOT23	3000/Tape & Reel
DMG3402L-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://:www.diodes.com/products/packages.html.

# **Marking Information**



N32 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

Year	201:	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		Α		В	(		D		E		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	±12	V
Drain Current (Note 5)	I <sub>D</sub>	4.0	А
Body-Diode Continuous Current (Note 5)	Is	1.5	А

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	1.4	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	90	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.6	_	1.4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
			_	52		$V_{GS} = 10V, I_D = 4A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		_	65	mΩ	$V_{GS} = 4.5V, I_D = 3A$	
			_	85		$V_{GS} = 2.5V, I_D = 2A$	
Forward Transconductance	Y <sub>fs</sub>	_	6.6	_	S	$V_{DS} = 5V, I_{D} = 3.1A$	
Source-Drain Diode Forward Voltage	$V_{SD}$	_	_	1.16	V	$V_{GS} = 0V, I_{S} = 2.0A$	
DYNAMIC CHARACTERISTICS(Note 7)							
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (10V)	Qg	_	11.7	_	nC	$V_{GS} = 10 \text{ V}, V_{DS} = 15 \text{V},$ $I_D = 4 \text{ A}$	
Total Gate Charge (4.5V)	Qq	_	5.5	_	nC	.,,	
Gate-Source Charge	Q <sub>qs</sub>	_	1.1	_	nC	$V_{GS} = 10 \text{ V}, V_{DS} = 15 \text{V},$	
Gate-Drain Charge	Q <sub>gd</sub>	_	1.8	_	nC	$I_D = 4 A$	
Turn-On Delay Time	t <sub>D(on)</sub>	_	1.9	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	1.6	_	ns	V <sub>DD</sub> = 15V, V <sub>GEN</sub> = 10V,	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	10.3	_	ns	$R_{GEN} = 3\Omega$ , $R_L = 3.75\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	2.0	_	ns		
Input Capacitance	C <sub>iss</sub>	_	464	_	pF		
Output Capacitance	Coss	_	49.5	_	pF	$V_{DS} = 15V, V_{GS} = 0V$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	43.8		pF	f = 1.0MHz	

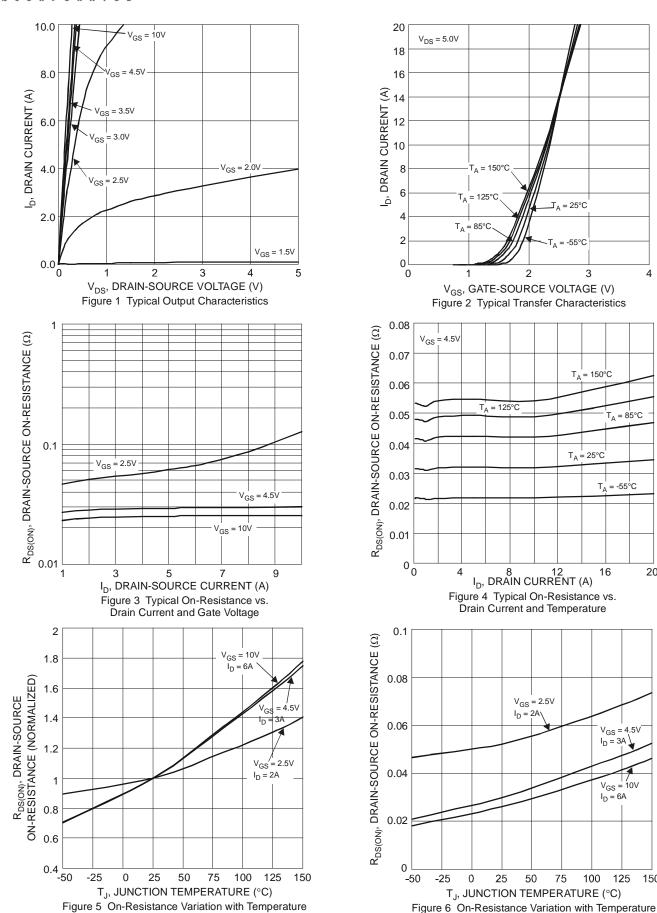
Notes:

- 5. Device mounted on FR-4 PCB. t ≤5 sec.
  6. Short duration pulse test used to minimize self-heating effect.
  7. Guaranteed by design. Not subject to production testing.

T<sub>A</sub> = 85°C

20





150

125

 $I_D = 3A$ 



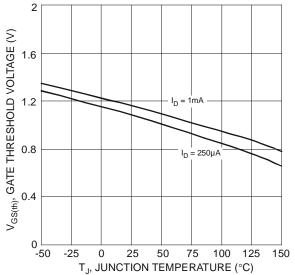
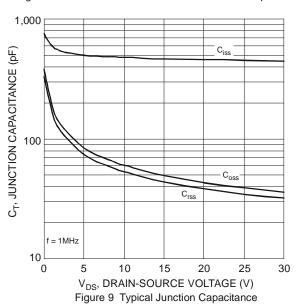
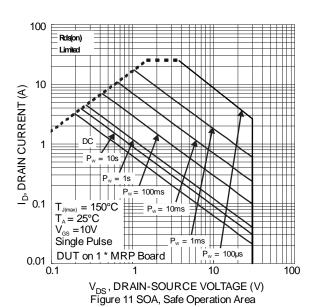
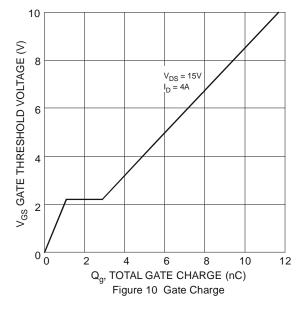


Figure 7 Gate Threshold Variation vs. Ambient Temperature

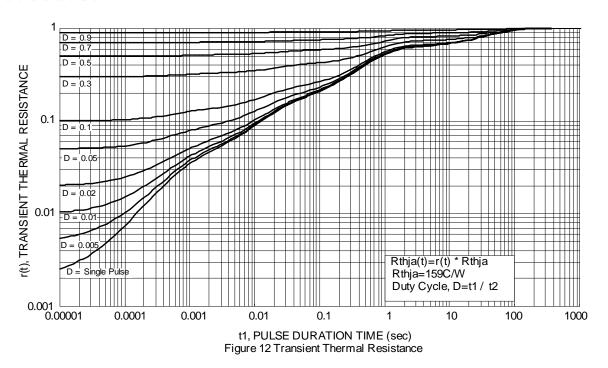




20 18 16 I<sub>S</sub>, SOURCE CURRENT (A) 12 10 T<sub>A</sub> = 25°C 8 6 2 0 0 0.6 0.9 1.2 1.5 V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current

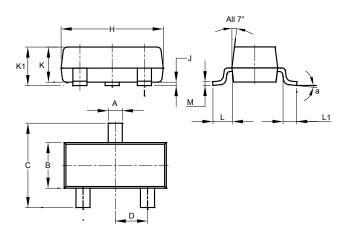






# **Package Outline Dimensions**

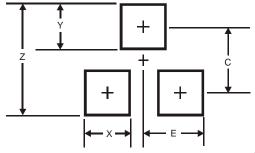
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	8°						
All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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